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December 2013

FQP13N10L

N-Channel QFET® MOSFET

100 V, 12.8 A, 180 $m\Omega$

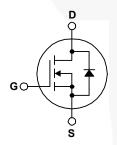
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 12.8 A, 100 V, $R_{DS(on)}$ = 180 m Ω (Max.) @ V_{GS} = 10 V, I_D = 6.4 A
- Low Gate Charge (Typ. 8.7 nC)
- · Low Crss (Typ. 20 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter			FQP13N10L	Unit	
V _{DSS}	Drain-Source Voltage			100	V	
I _D	Drain Current	- Continuous (T _C = 25°C)		12.8	Α	
		- Continuous (T _C = 100°C)		9.05	Α	
I _{DM}	Drain Current	- Pulsed	(Note 1)	51.2	А	
V _{GSS}	Gate-Source Voltage			± 20	V	
E _{AS}	Single Pulsed Avalanche Energy (No		(Note 2)	95	mJ	
I _{AR}	Avalanche Current		(Note 1)	12.8	А	
E _{AR}	Repetitive Avalanche Energy		(Note 1)	6.5	mJ	
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	6.0	V/ns	
P_D	Power Dissipation (T _C = 25°C)			65	W	
	- Derate above 25°C			0.43	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +175	°C	
T _L	Maximum lead temperature for soldering, 1/8" from case for 5 seconds.			300	°C	

Thermal Characteristics

Symbol	Parameter	FQP13N10L	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.31	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP13N10L	FQP13N10L	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	racteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		0.09		V/°C
I _{DSS}	Zara Cata Valtana Dunin Comment	V _{DS} = 100 V, V _{GS} = 0 V			1	μА
	Zero Gate Voltage Drain Current	$V_{DS} = 80 \text{ V}, T_{C} = 150^{\circ}\text{C}$			10	μА
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -20 V, V _{DS} = 0 V			-100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0		2.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 6.4 \text{ A}$ $V_{GS} = 5 \text{ V}, I_D = 6.4 \text{ A}$		0.142 0.158	0.18 0.2	Ω
9 _{FS}	Forward Transconductance $V_{DS} = 30 \text{ V}, I_D = 6.4 \text{ A}$			9.5		S
	ic Characteristics				T	
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1.0 \text{ MHz}$		400	520	pF
C _{oss}	Output Capacitance			95	125	pF
C _{rss}	Reverse Transfer Capacitance			20	25	pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 50 \text{ V}, I_{D} = 12.8 \text{ A},$ $R_{G} = 25 \Omega$		7.5	25	ns
t _r	Turn-On Rise Time			220	450	ns
t _{d(off)}	Turn-Off Delay Time	1.13 2011		22	55	ns
t _f	Turn-Off Fall Time	(Note 4)		72	150	ns
Qg	Total Gate Charge	V _{DS} = 80 V, I _D = 12.8 A,		8.7	12	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = 5 V$ (Note 4)		2.0		nC
Q _{gd}	Gate-Drain Charge			5.3		nC
Drain-S	ource Diode Characteristics a	nd Maximum Ratings	/			
I _S	Maximum Continuous Drain-Source Diode Forward Current				12.8	Α
I _{SM}	Maximum Pulsed Drain-Source Diode F	Forward Current			51.2	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 12.8 A			1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 12.8 A,		75		ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		0.17	//	μС

Notes: 1. Repetitive rating : pulse-width limited by maximum junction temperature. 2. L = 0.87 mH, I_{AS} = 12.8 A, V_{DD} = 25 V, R_G = 25 Ω starting T_J = 25°.C 3. I_{SD} \leq 12.8 A, di/dt \leq 300 A/ μ s, V_{DD} \leq BV_{DSS}, starting T_J = 25°C. 4. Essentially independent of operating temperature.

Typical Characteristics

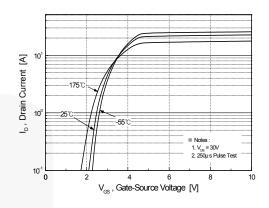


Figure 2. Transfer Characteristics

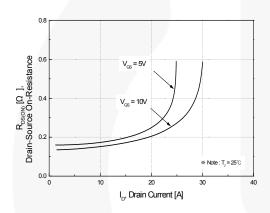


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

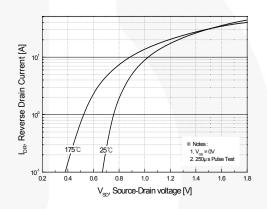


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

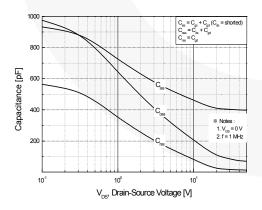


Figure 5. Capacitance Characteristics

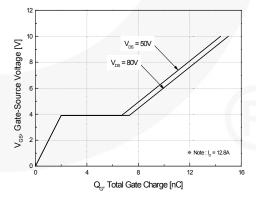


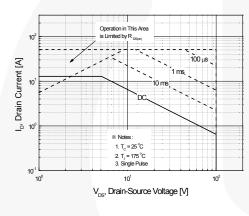
Figure 6. Gate Charge Characteristics

12 (γοωπαίτος Γ°C) ** Notes: 1. / (γω = 0 V) 2. / (μω = 0 V) 2. / (μω = 0 V) 3. / (μω = 0 V) 3. / (μω = 0 V) 4. / (μω = 0 V) 5. / (μω = 0 V) 7. / (μω

Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



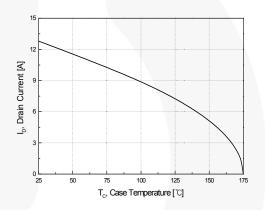


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

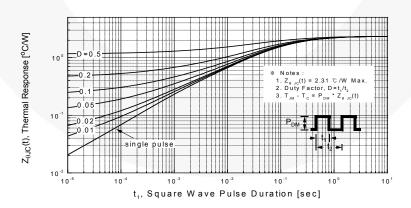


Figure 11. Transient Thermal Response Curve

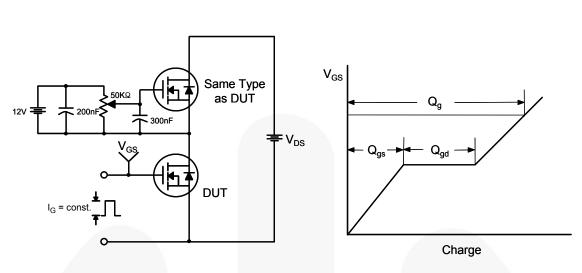


Figure 12. Gate Charge Test Circuit & Waveform

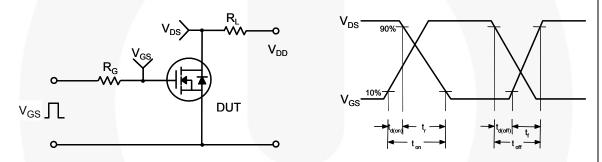


Figure 13. Resistive Switching Test Circuit & Waveforms

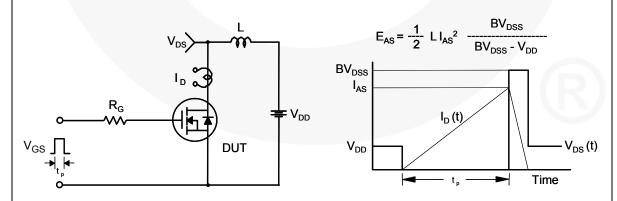
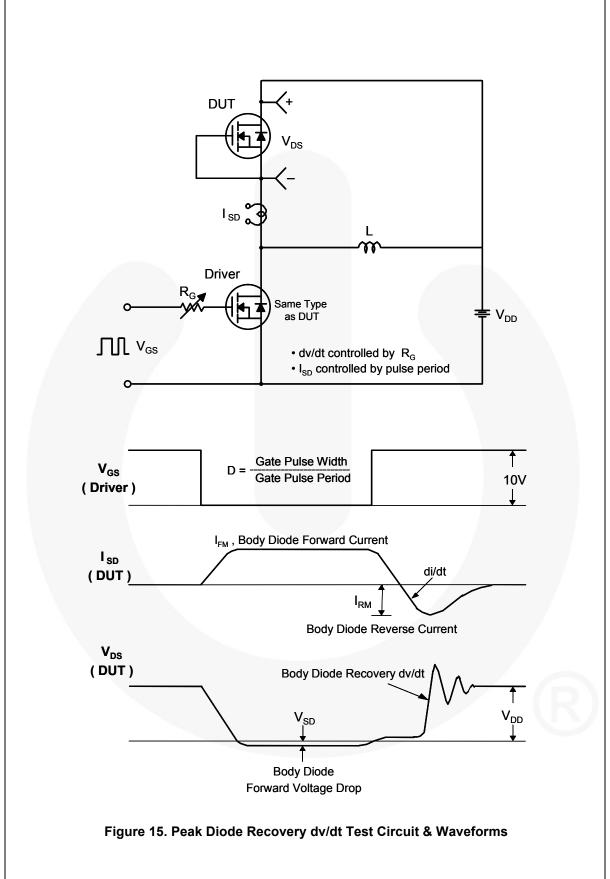


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

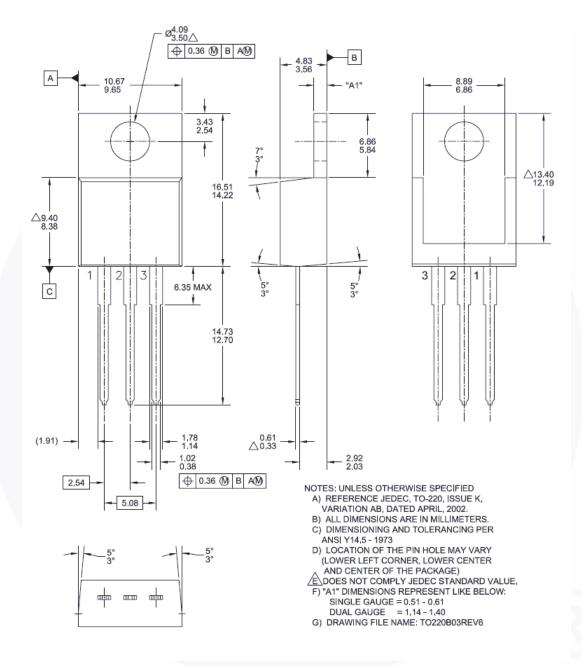


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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